

/ Descriptions

GIQ6×6D0;0 M M Q P R V J ǝ ǝ Z 1
N-Channel Enhancement Mode Field Effect Transistor in a DFN3×3A-8L Plastic Package.

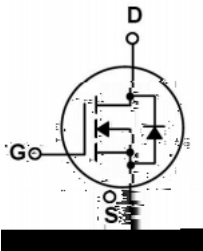
/ Features

$V_{DS} (V) = 20V$ $I_D = 43A (V_{GS} = \pm 12V)$
 $R_{DS(ON)}@10V \leq 10m\Omega (Typ.8.0m\Omega)$
 $R_{DS(ON)}@4.5V \leq 11m\Omega (Typ.9.5m\Omega)$
 $R_{DS(ON)}@2.5V \leq 16m\Omega (Typ.14m\Omega)$
 η β HF Product.

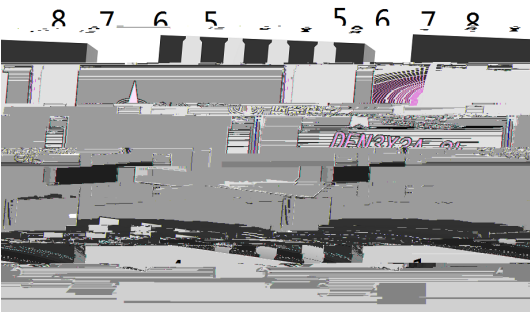
/ Applications

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Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

/ Equivalent Circuit



/ Pinning



出脚	定义
Pin1	S
Pin2	S
4	S
5	S
6	S
7	S
8	S

/ Marking

M ǝ "
See Marking Instructions.

参数名称 Parameter Name		符号 Symbol	单位 Unit	典型值 Typical Value
漏极-源极饱和电压 Drain-Source Saturation Voltage		$V_{DS(sat)}$	V	53
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	76
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	43
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	±45
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	45±8
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	444
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	5
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	483
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	088 483
漏极-源极击穿电压 Drain-Source Breakdown Voltage	$V_{DS(BO)}$	$V_{DS(BO)}$	V	83
	$V_{DS(BO)}$			±3
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	718
漏极-源极击穿电压 Drain-Source Breakdown Voltage		$V_{DS(BO)}$	V	2 Z

参数名称 Parameter Name	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
漏极-源极击穿电压 Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu$				

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	t _{d(on)}	V _{DS} =10V V _{GS} =10V R _L =1.0Ω R _{GEN} =3.0Ω		2.5		ns
Turn-On Rise Time	t _r			7.2		
Turn-Off Delay Time	t _{d(off)}			49		
Turn-Off Fall Time	t _f			10.8		
Total Gate Charge	Q _{g(4.5V)}	V _{DS} =10V V _{GS} =4.5V I _D =12.0A		17.9		nC
Gate-Source Charge	Q _{gs}			1.5		
Gate-Drain Charge	Q _{gd}			4.7		

/ Electrical Characteristic Curve

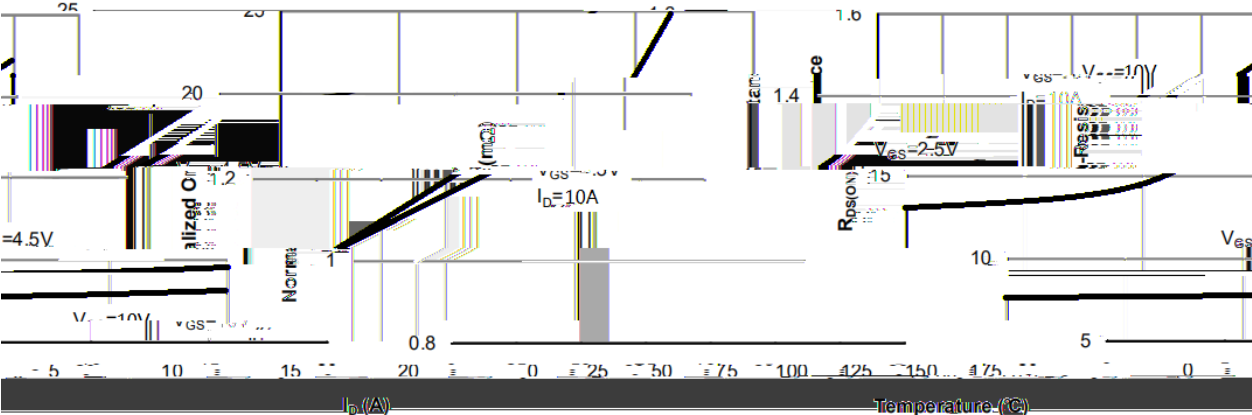
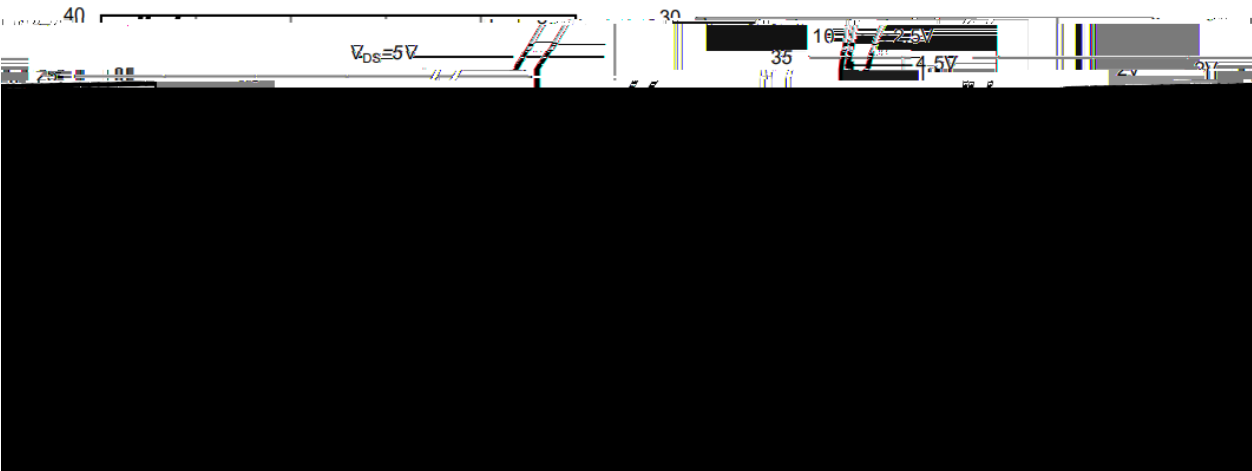
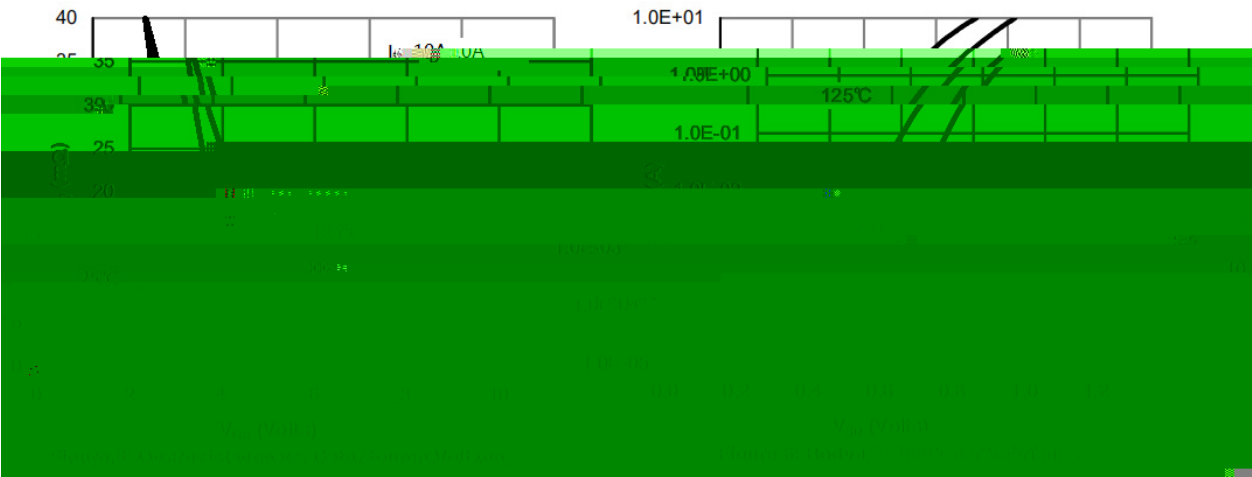
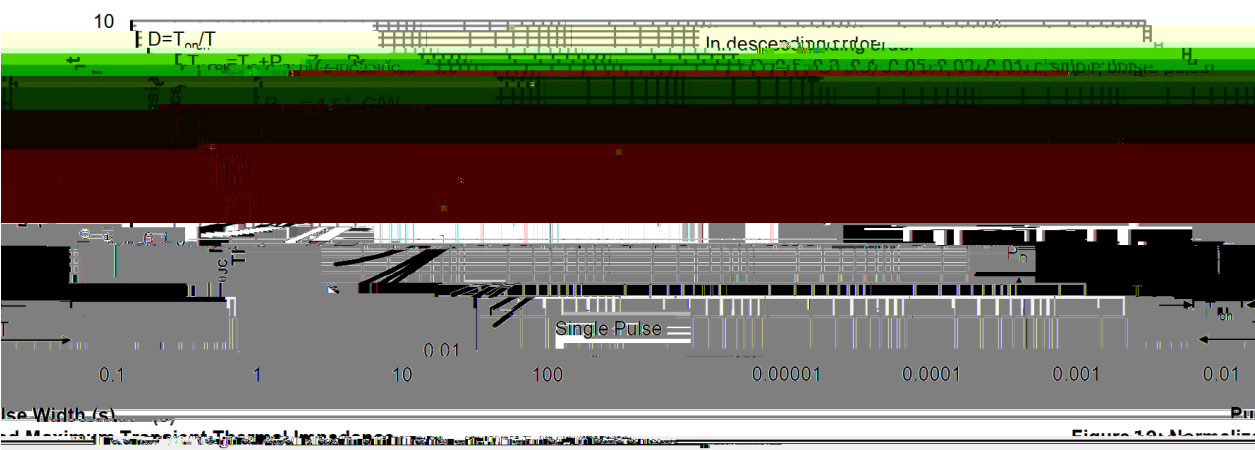
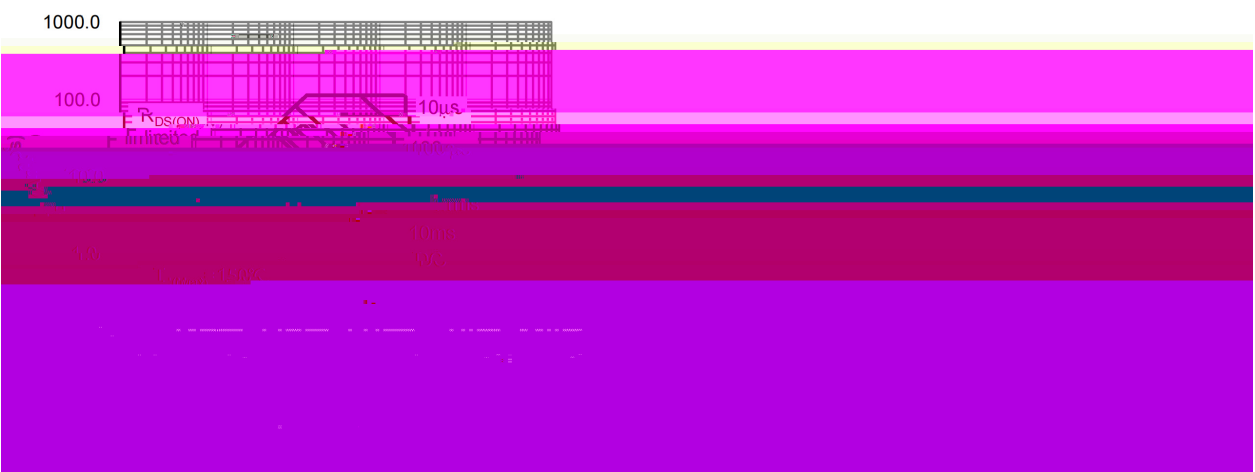
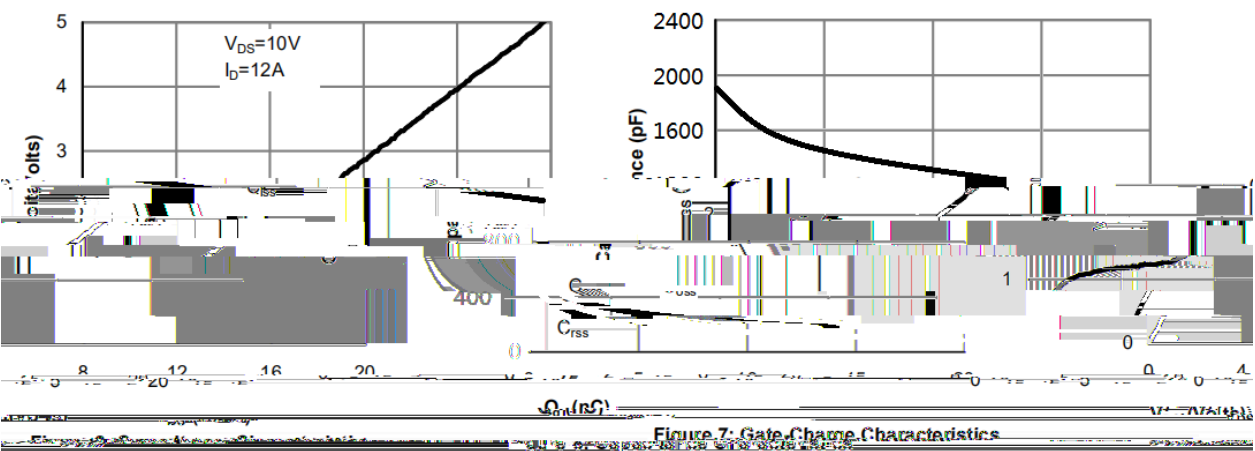


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Junction Temperature



/ Electrical Characteristic Curve



/ Package Dimensions

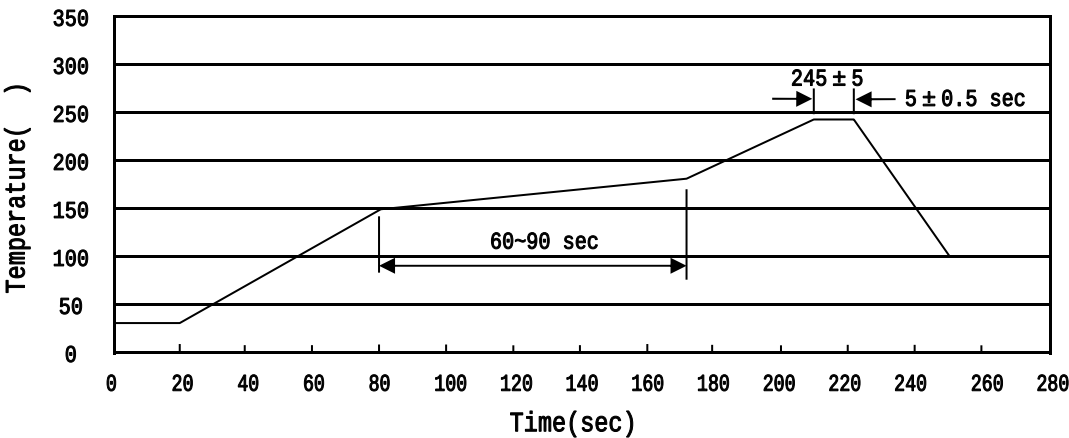


/ Marking Instructions



”	
BR	公司代码
080N02	产品型号
****	批次号
Note:	
BR:	Company Code
080N02:	Product Type Code
****:	Lot No. Code, code change with Lot No

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- Note:
1. Preheating:150~180 , Time:60~90sec;

2. Peak Temp.:245±5 , Duration:5±0.5sec;

3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

□ ° 260±5 °H 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

□ ° / REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
DFN3×3A-8L	5,000	2	10,000	6	60,000	13 ×12	360×360×50	380×335×366

/ Notices